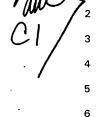
IN THE CLAIMS:

Please cancel claims 1-17 without prejudice.

Please add new claims 21-37.



--21. (New) An integrated circuit includes a gate structure disposed over a channel, a deep source region heavily doped with dopants of a first conductivity type, a deep drain region heavily doped with dopants of the first conductivity type, a source extension integral the deep source region, and a drain extension integral the deep drain region, wherein the drain extension is deeper than the source extension, wherein the integrated circuit is manufactured by a method, comprising:

7

8

9

providing the gate structure between a source location and a drain location in a semiconductor substrate;

10

providing an angled source extension implant in a direction from the source location to the drain location;

11 12

providing an Angled drain extension implant in a direction from the

13

drain location to the source location; and

14

providing/a deep source/drain implant at the source location and

15

the drain location.

1 2

3

22. (New) The integrated circuit of claim 21, further comprising providing a pair of spacefrs abutting lateral sides of the gate structure before the deep source drain/implant.

23. (New) The integrated circuit of claim 22, wherein the providing the source extension step is a low energy, high dose ion implantation step.

2

3

2

3

2

3

4

1

2

1

2

1

2

1

2

3

4

5

6

7

- 24. (New) The integrated circuit of claim 23, wherein the drain extension implant step is a medium energy, high dose ion implantation step.
 - 25. (New) The integrated orcuit of claim 24, wherein a source extension formed by the source extension step is shallower than a drain extension formed by the drain extension implant step.
 - 26. (New) The integrated circuit of claim 25, wherein the source extension has approximately 5 times the concentration of dopants of the drain extension.
 - 27. (New) The integrated circuit of claim 25, wherein the source extension has a concentration of $5x10^{19}-1x10^{20}$ of dopants per centimeter cubed and the drain extension has a concentration of $1x10^{19}-5x10^{19}$ dopants per centimeter cubed.
 - 28. (New) The integrated circuit of claim 25, wherein the drain extension has a concentration between $1x10^{19} 5x10^{19}$ dopants per centimeter cubed.
- 29. (New) The integrated circuit of claim 25, wherein the drain extension is more than 80 nm deep.
- 30. (New) The integrated circuit of claim 27, wherein the gate structure is associated with a N-channel or P-channel with MOSFET.



- 31. (New) An ultra-large scale integrated circuit including a plurality of field effect transistors, the field effect transistors comprising:
 - a gate structure on a top surface of a semiconductor substrate;
- a source extension with dopants of a first conductivity type;
 - a drain extension with dopants of the first conductivity type; and
 - forming deep source and drain regions with dopants of the first
- conductivity type, wherein the gate structure is between the source and drain
- regions, wherein the drain extension is deeper than the source extension.